



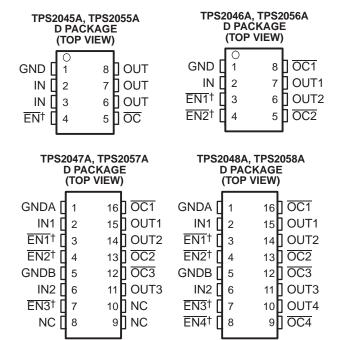
CURRENT-LIMITED POWER-DISTRIBUTION SWITCHES

FEATURES

- 80-mΩ High-Side MOSFET Switch
- 250 mA Continuous Current Per Channel
- Independent Thermal and Short-Circuit Protection With Overcurrent Logic Output
- Operating Range: 2.7-V to 5.5-V
- CMOS- and TTL-Compatible Enable Inputs
- 2.5-ms Typical Rise Time
- Undervoltage Lockout
- 10 μA Maximum Standby Supply Current for Single and Dual (20 μA for Triple and Quad)
- Bidirectional Switch
- Ambient Temperature Range, 0°C to 85°C
- ESD Protection

DESCRIPTION

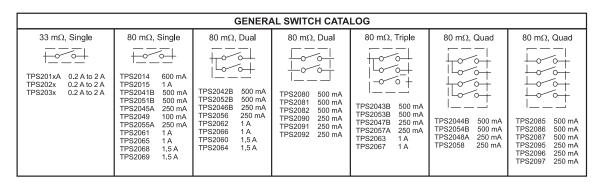
The TPS2045A through TPS2048A and TPS2055A through TPS2058A power-distribution switches are intended for applications where heavy capacitive loads and short circuits are likely to be encountered.



 † All enable inputs are active high for the TPS205xA series. NC - No connect

These devices incorporate $80\text{-m}\Omega$ N-channel MOSFET high-side power switches for power-distribution systems that require multiple power switches in a single package. Each switch is controlled by an independent logic enable input. Gate drive is provided by an internal charge pump designed to control the power-switch rise times and fall times to minimize current surges during switching. The charge pump requires no external components and allows operation from supplies as low as 2.7 V.

When the output load exceeds the current-limit threshold or a short is present, these devices limit the output current to a safe level by switching into a constant-current mode, pulling the overcurrent (\overline{OCx}) logic output low. When continuous heavy overloads and short circuits increase the power dissipation in the switch, causing the junction temperature to rise, a thermal protection circuit shuts off the switch to prevent damage. Recovery from a thermal shutdown is automatic once the device has cooled sufficiently. Internal circuitry ensures the switch remains off until valid input voltage is present. These power-distribution switches are designed to current limit at 0.5 A.





Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

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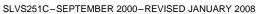
These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

AVAILABLE OPTIONS(1)

		RECOMMENDED	TYPICAL SHORT-CIRCUIT		PACKAGED DEVICES
TA	ENABLE	MAXIMUM CONTINUOUS LOAD CURRENT (A)	CURRENT LIMIT AT 25°C (A)	NUMBER OF SWITCHES	SOIC (D) ⁽²⁾
	Active low			Cinalo	TPS2045AD
	Active high		0.5	Single	TPS2055AD
	Active low			Dual	TPS2046AD
0°C to 85°C	Active high	0.25		Duai	TPS2056AD
0 0 10 65 0	Active low	0.25	0.5	Triple	TPS2047AD
	Active high			Triple	TPS2057AD
Active lo	Active low			Quad	TPS2048AD
	Active high			Quad	TPS2058AD

⁽¹⁾ For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI website at www.ti.com.

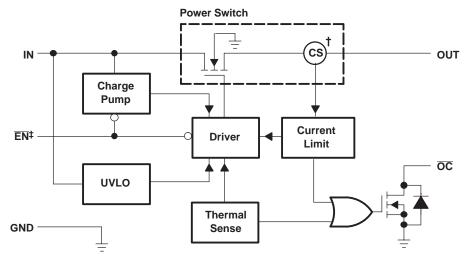
⁽²⁾ The D package is available taped and reeled. Add an R suffix to device type (e.g., TPS2045ADR)





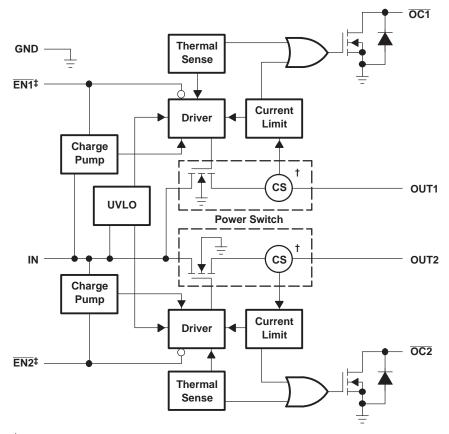
FUNCTIONAL BLOCK DIAGRAMS

TPS2045A



- † Current sense
- [‡] Active high for TPS205xA series

TPS2046A

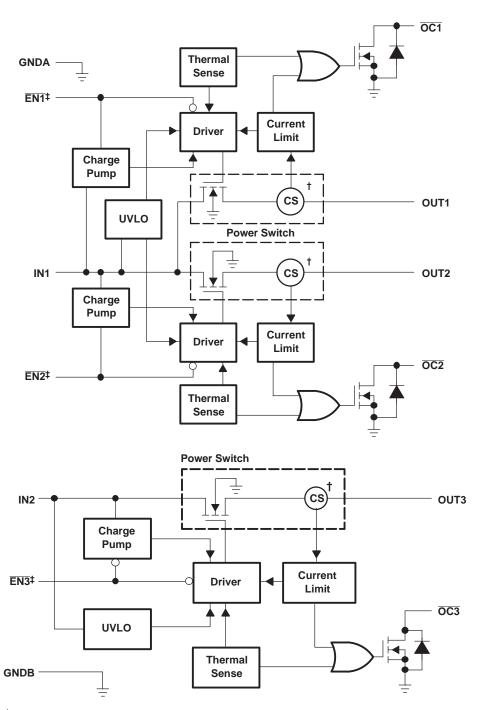


[†] Current sense

[‡] Active high for TPS205xA series



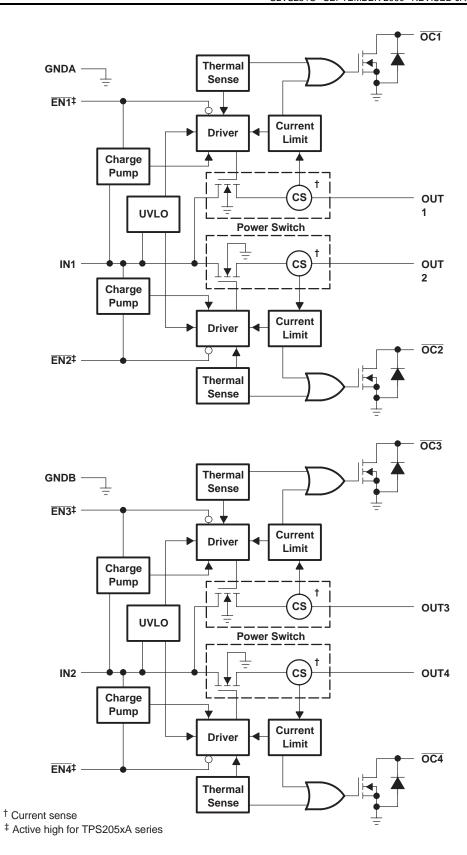
TPS2047A



- † Current sense
- [‡] Active high for TPS205xA series



TPS2048A



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Terminal Functions

			Terminal Functions				
A AND TPS2	055A						
TERMINA	_						
N	0.	I/O	DESCRIPTION				
TPS2045A	TPS2055A						
4	•	I	Enable input. Logic low turns on power switch.				
-	4	I	Enable input. Logic high turns on power switch.				
1	1	I	Ground				
2, 3	2, 3	I	Input voltage				
5	5	0	Overcurrent. Open drain output active low				
OUT 6, 7, 8 6, 7, 8		0	Power-switch output				
SA AND TPS2	056A	•					
TERMINA	<u>L</u>						
NO.		NO.		I/O	DESCRIPTION		
TPS2046A	A TPS2056A						
3	=	I	Enable input. Logic low turns on power switch, IN-OUT1.				
4	•	I	Enable input. Logic low turns on power switch, IN-OUT2.				
-	3	I	Enable input. Logic high turns on power switch, IN-OUT1.				
-	4	I	Enable input. Logic high turns on power switch, IN-OUT2.				
1	1	I	Ground				
2	2	I	Input voltage				
8	8	0	Overcurrent. Open drain output active low, for power switch, IN-OUT1				
5	5	0	Overcurrent. Open drain output active low, for power switch, IN-OUT2				
7	7	0	Power-switch output				
6	6	0	Power-switch output				
	TERMINAI NOTPS2045A 4 - 1 2, 3 5 6, 7, 8 6A AND TPS20 TERMINAI NOTPS2046A 3 4 1 2 8 5 7	4 - 4 1 1 1 2, 3 2, 3 5 5 6, 7, 8 6, 7, 8 6A AND TPS2056A TERMINAL NO. TPS2046A TPS2056A 3 - 4 - 3 - 4 1 1 1 2 2 8 8 8 5 7 7	NO. I/O TPS2045A TPS2055A				



Terminal Functions (continued)

	TERMINA	L					
NAME	N	0.	I/O	DESCRIPTION			
INAIVIE	TPS2047A	TPS2057A					
EN1	3	-	I	Enable input, logic low turns on power switch, IN1-OUT1.			
EN2	4	-	I	Enable input, logic low turns on power switch, IN1-OUT2.			
EN3	7	ı	I	Enable input, logic low turns on power switch, IN2-OUT3.			
EN1	-	3	ı	Enable input, logic high turns on power switch, IN1-OUT1.			
EN2	-	4	I	Enable input, logic high turns on power switch, IN1-OUT2.			
EN3	-	7	I	Enable input, logic high turns on power switch, IN2-OUT3.			
GNDA	1	1		Ground for IN1 switch and circuitry.			
GNDB	5	5		Ground for IN2 switch and circuitry.			
IN1	2	2	ı	Input voltage			
IN2	6	6	I	Input voltage			
NC	8, 9, 10	8, 9, 10		No connection			
OC1	16	16	0	Overcurrent, open drain output active low, IN1-OUT1			
OC2	13	13	0	Overcurrent, open drain output active low, IN1-OUT2			
OC3	12	12	0	Overcurrent, open drain output active low, IN2-OUT3			
OUT1	15	15	0	wer-switch output, IN1-OUT1			
OUT2	14	14	0	Power-switch output, IN1-OUT2			
OUT3	11	11	0	Power-switch output, IN2-OUT3			
TPS2048	BA AND TPS2	058A					
	TERMINA	L					
NAME	N	0.	I/O	DESCRIPTION			
IVAIVIL	TPS2048A	TPS2058A					
EN1	3	=	ı	Enable input. logic low turns on power switch, IN1-OUT1.			
EN2	4	-	- 1	Enable input. Logic low turns on power switch, IN1-OUT2.			
EN3	7						
		-	I	Enable input. Logic low turns on power switch, IN2-OUT3.			
EN4	8	-	l I	Enable input. Logic low turns on power switch, IN2-OUT3. Enable input. Logic low turns on power switch, IN2-OUT4.			
EN4 EN1	8 -						
		-	ı	Enable input. Logic low turns on power switch, IN2-OUT4.			
EN1		3		Enable input. Logic low turns on power switch, IN2-OUT4. Enable input. Logic high turns on power switch, IN1-OUT1.			
EN1 EN2	-	- 3 4	1 1 1	Enable input. Logic low turns on power switch, IN2-OUT4. Enable input. Logic high turns on power switch, IN1-OUT1. Enable input. Logic high turns on power switch, IN1-OUT2.			
EN1 EN2 EN3		- 3 4 7		Enable input. Logic low turns on power switch, IN2-OUT4. Enable input. Logic high turns on power switch, IN1-OUT1. Enable input. Logic high turns on power switch, IN1-OUT2. Enable input. Logic high turns on power switch, IN2-OUT3.			
EN1 EN2 EN3 EN4	- - -	- 3 4 7 8		Enable input. Logic low turns on power switch, IN2-OUT4. Enable input. Logic high turns on power switch, IN1-OUT1. Enable input. Logic high turns on power switch, IN1-OUT2. Enable input. Logic high turns on power switch, IN2-OUT3. Enable input. Logic high turns on power switch, IN2-OUT4. Ground for IN1 switch and circuitry. Ground for IN2 switch and circuitry.			
EN1 EN2 EN3 EN4 GNDA	- - - - 1	- 3 4 7 8		Enable input. Logic low turns on power switch, IN2-OUT4. Enable input. Logic high turns on power switch, IN1-OUT1. Enable input. Logic high turns on power switch, IN1-OUT2. Enable input. Logic high turns on power switch, IN2-OUT3. Enable input. Logic high turns on power switch, IN2-OUT4. Ground for IN1 switch and circuitry.			
EN1 EN2 EN3 EN4 GNDA GNDB	- - - - 1	- 3 4 7 8 1	1 1 1	Enable input. Logic low turns on power switch, IN2-OUT4. Enable input. Logic high turns on power switch, IN1-OUT1. Enable input. Logic high turns on power switch, IN1-OUT2. Enable input. Logic high turns on power switch, IN2-OUT3. Enable input. Logic high turns on power switch, IN2-OUT4. Ground for IN1 switch and circuitry. Ground for IN2 switch and circuitry.			
EN1 EN2 EN3 EN4 GNDA GNDB IN1 IN2 OC1	- - - - 1 5	- 3 4 7 8 1 5	1 1 1 1	Enable input. Logic low turns on power switch, IN2-OUT4. Enable input. Logic high turns on power switch, IN1-OUT1. Enable input. Logic high turns on power switch, IN1-OUT2. Enable input. Logic high turns on power switch, IN2-OUT3. Enable input. Logic high turns on power switch, IN2-OUT4. Ground for IN1 switch and circuitry. Ground for IN2 switch and circuitry. Input voltage			
EN1 EN2 EN3 EN4 GNDA GNDB IN1 IN2 OC1 OC2	- - - - 1 5 2	- 3 4 7 8 1 5 2		Enable input. Logic low turns on power switch, IN2-OUT4. Enable input. Logic high turns on power switch, IN1-OUT1. Enable input. Logic high turns on power switch, IN1-OUT2. Enable input. Logic high turns on power switch, IN2-OUT3. Enable input. Logic high turns on power switch, IN2-OUT4. Ground for IN1 switch and circuitry. Ground for IN2 switch and circuitry. Input voltage Input voltage			
EN1 EN2 EN3 EN4 GNDA GNDB IN1 IN2 OC1	- - - - 1 5 2 6 16	- 3 4 7 8 1 5 2 6		Enable input. Logic low turns on power switch, IN2-OUT4. Enable input. Logic high turns on power switch, IN1-OUT1. Enable input. Logic high turns on power switch, IN1-OUT2. Enable input. Logic high turns on power switch, IN2-OUT3. Enable input. Logic high turns on power switch, IN2-OUT4. Ground for IN1 switch and circuitry. Ground for IN2 switch and circuitry. Input voltage Input voltage Overcurrent. Open drain output active low, IN1-OUT1			
EN1 EN2 EN3 EN4 GNDA GNDB IN1 IN2 OC1	- - - - 1 5 2 6 16	- 3 4 7 8 1 5 2 6 16		Enable input. Logic low turns on power switch, IN2-OUT4. Enable input. Logic high turns on power switch, IN1-OUT1. Enable input. Logic high turns on power switch, IN1-OUT2. Enable input. Logic high turns on power switch, IN2-OUT3. Enable input. Logic high turns on power switch, IN2-OUT4. Ground for IN1 switch and circuitry. Ground for IN2 switch and circuitry. Input voltage Input voltage Overcurrent. Open drain output active low, IN1-OUT1 Overcurrent. Open drain output active low, IN1-OUT2			
EN1 EN2 EN3 EN4 GNDA GNDB IN1 IN2 OC1 OC2 OC3	- - - - 1 5 2 6 16 13	- 3 4 7 8 1 5 2 6 16 13		Enable input. Logic low turns on power switch, IN2-OUT4. Enable input. Logic high turns on power switch, IN1-OUT1. Enable input. Logic high turns on power switch, IN1-OUT2. Enable input. Logic high turns on power switch, IN2-OUT3. Enable input. Logic high turns on power switch, IN2-OUT4. Ground for IN1 switch and circuitry. Ground for IN2 switch and circuitry. Input voltage Input voltage Overcurrent. Open drain output active low, IN1-OUT1 Overcurrent. Open drain output active low, IN1-OUT3			
EN1 EN2 EN3 EN4 GNDA GNDB IN1 IN2 OC1 OC2 OC3 OC4	- - - - 1 5 2 6 16 13 12	- 3 4 7 8 1 5 2 6 16 13 12 9		Enable input. Logic low turns on power switch, IN2-OUT4. Enable input. Logic high turns on power switch, IN1-OUT1. Enable input. Logic high turns on power switch, IN1-OUT2. Enable input. Logic high turns on power switch, IN2-OUT3. Enable input. Logic high turns on power switch, IN2-OUT4. Ground for IN1 switch and circuitry. Ground for IN2 switch and circuitry. Input voltage Input voltage Overcurrent. Open drain output active low, IN1-OUT1 Overcurrent. Open drain output active low, IN1-OUT3 Overcurrent. Open drain output active low, IN2-OUT3 Overcurrent. Open drain output active low, IN2-OUT4			

10

0

10

OUT4

Power-switch output, IN2-OUT4

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DETAILED DESCRIPTION

POWER SWITCH

The power switch is an N-channel MOSFET with a maximum on-state resistance of 135 m Ω ($V_{I(IN)} = 5$ V). Configured as a high-side switch, the power switch prevents current flow from OUT to IN and IN to OUT when disabled. The power switch supplies a minimum of 250 mA per switch.

CHARGE PUMP

An internal charge pump supplies power to the driver circuit and provides the necessary voltage to pull the gate of the MOSFET above the source. The charge pump operates from input voltages as low as 2.7 V and requires very little supply current.

DRIVER

The driver controls the gate voltage of the power switch. To limit large current surges and reduce the associated electromagnetic interference (EMI) produced, the driver incorporates circuitry that controls the rise times and fall times of the output voltage. The rise and fall times are typically in the 2-ms to 4-ms range.

ENABLE (ENX, ENX)

The logic enable disables the power switch and the bias for the charge pump, driver, and other circuitry to reduce the supply current. The supply current is reduced to less than 10 μ A on the single and dual devices (20 μ A on the triple and quad devices) when a logic high is present on \overline{ENx} (TPS204xA 1) or a logic low is present on ENx (TPS205xA 1). A logic zero input on \overline{ENx} or a logic high on ENx restores bias to the drive and control circuits and turns the power on. The enable input is compatible with both TTL and CMOS logic levels.

OVERCURRENT (OCx)

The \overline{OCx} open-drain output is asserted (active low) when an overcurrent or over temperature condition is encountered. The output will remain asserted until the overcurrent or over temperature condition is removed.

CURRENT SENSE

A sense FET monitors the current supplied to the load. The sense FET measures current more efficiently than conventional resistance methods. When an overload or short circuit is encountered, the current-sense circuitry sends a control signal to the driver. The driver in turn reduces the gate voltage and drives the power FET into its saturation region, which switches the output into a constant-current mode and holds the current constant while varying the voltage on the load.

THERMAL SENSE

The TPS204xA and TPS205xA implement a dual-threshold thermal trip to allow fully independent operation of the power distribution switches. In an overcurrent or short-circuit condition the junction temperature rises. When the die temperature rises to approximately 140° C, the internal thermal sense circuitry checks to determine which power switch is in an overcurrent condition and turns off that switch, thus isolating the fault without interrupting operation of the adjacent power switch. Hysteresis is built into the thermal sense, and after the device has cooled approximately 20 degrees, the switch turns back on. The switch continues to cycle off and on until the fault is removed. The (\overline{OCx}) open-drain output is asserted (active low) when over temperature or overcurrent occurs.

UNDERVOLTAGE LOCKOUT

A voltage sense circuit monitors the input voltage. When the input voltage is below approximately 2 V, a control signal turns off the power switch.



ABSOLUTE MAXIMUM RATINGS

over operating free-air temperature range (unless otherwise noted)(1)

			UNIT
V _{I(IN)}	Input voltage range (2)		0.3 V to 6 V
V _{O(OUT)}	Output voltage range ⁽²⁾		$-0.3 \text{ V to V}_{\text{I(IN)}} + 0.3 \text{ V}$
V _{I(ENx)} or V _{I(ENx)}	Input voltage range		–0.3 V to 6 V
I _{O(OUT)}	Continuous output current		internally limited
	Continuous total power dissipation		See Dissipation Rating Table
T _J	Operating virtual junction temperature range		0°C to 125°C
T _{stg}	Storage temperature range		−65°C to 150°C
	Lead temperature soldering 1,6 mm (1/16 inc	h) from case for 10 seconds	260°C
ECD		Human body model MIL-STD-883C	2 kV
ESD	Electrostatic discharge protection	Machine model	0.2 kV

⁽¹⁾ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

DISSIPATION RATING TABLE

PACKAGE	T _A ≤ 25°C POWER RATING	DERATING FACTOR ABOVE T _A = 25°C	T _A = 70°C POWER RATING	T _A = 85°C POWER RATING
D-8	725 mW	5.9 mW/°C	464 mW	377 mW
D-16	1123 mW	9 mW/°C	719 mW	584 mW

RECOMMENDED OPERATING CONDITIONS

		MIN	MAX	UNIT
$V_{I(IN)}$	Input voltage	2.7	5.5	V
$V_{I(EN)}$ or $V_{I(EN)}$	Input voltage	0	5.5	V
I _{O(OUT)}	Continuous output current (per switch)	0	250	mA
TJ	Operating virtual junction temperature	0	125	°C

⁽²⁾ All voltages are with respect to GND.



ELECTRICAL CHARACTERISTICS OVER RECOMMENDED OPERATING JUNCTION TEMPERATURE RANGE

 $V_{I(IN)} = 5.5 \text{ V}, I_O = \text{rated current}, V_{I(EN)} = V_{I(IN)} \text{(unless otherwise noted)}$

	DADAMETED	TEST CONI	OUTLONIC(1)	TI	PS204xA	١	TI	PS205x	4	LINUT
	PARAMETER	TEST CONL	DITIONS	MIN	TYP	MAX	MIN	TYP	MAX	UNIT
		$V_{I(IN)} = 5 \text{ V},$ $I_O = 0.25 \text{ A}$	$T_J = 25^{\circ}C$,		80	100		80	100	
	Static drain-source on-state resistance, 5-V operation	$V_{I(IN)} = 5 \text{ V},$ $I_O = 0.25 \text{ A}$	$T_J = 85^{\circ}C$,		90	120		90	120	
		$V_{I(IN)} = 5 \text{ V},$ $I_O = 0.25 \text{ A}$	$T_J = 125^{\circ}C$,		100	135		100	135	mΩ
r _{DS(on)}		$V_{I(IN)} = 3.3 \text{ V},$ $I_O = 0.25 \text{ A}$	$T_J = 25^{\circ}C$,		90	125		90	125	11177
	Static drain-source on-state resistance, 3.3-V operation	$V_{I(IN)} = 3.3 \text{ V},$ $I_O = 0.25 \text{ A}$	$T_J = 85^{\circ}C$,		110	145		110	145	
		$V_{I(IN)} = 3.3 \text{ V},$ $I_O = 0.25 \text{ A}$	$T_J = 125^{\circ}C$,		120	160		120	90 125 110 145 120 160 2.5	
+	Rise time, output	$V_{I(IN)} = 5.5 \text{ V},$ $C_L = 1 \mu\text{F},$	$T_J = 25^{\circ}C$, $R_L = 20\Omega$		2.5			2.5		ms
t _r	Kise time, output	$\begin{aligned} V_{I(IN)} &= 2.7 \text{ V}, \\ C_L &= 1 \mu\text{F}, \end{aligned}$	$T_J = 25^{\circ}C$, $R_L = 20\Omega$		3			3		1115
	Fall time output	$V_{I(IN)} = 5.5 \text{ V},$ $C_L = 1 \mu\text{F},$	$T_J = 25^{\circ}C$, $R_L = 20\Omega$		4.4			4.4		ma
t _f	Fall time, output	$V_{I(IN)} = 2.7 \text{ V},$ $C_L = 1 \mu\text{F},$			2.5			2.5		ms

⁽¹⁾ Pulse-testing techniques maintain junction temperature close to ambient temperature; thermal effects must be taken into account separately.

ENABLE INPUT ENX OR ENX

	PARAME	TED	TEST CONDITIONS		TPS204xA			TPS205xA			
	PARAIVIE	IER	TEST CONDITIONS	MIN	TYP	MAX	MIN	TYP	MAX	UNIT	
V_{IH}	high-level input	voltage	2.7 V ≤ V _{I(IN)} ≤ 5.5 V	2			2			٧	
\/	Low lovel inputs	rolto ao	$4.5 \text{ V} \le \text{V}_{\text{I(IN)}} \le 5.5 \text{ V}$			0.8			0.8	V	
V_{IL}	Low-level input voltage		2.7 V ≤ V _{I(IN)} ≤ 4.5 V			0.4			0.4	V	
	Input ourront	TPS204xA	$V_{I(ENX)} = 0 \text{ V or } V_{I(ENX)} = V_{I(IN)}$	-0.5		0.5				^	
"	Input current	TPS205xA	$V_{I(ENx)} = V_{I(IN)}$ or $V_{I(ENx)} = 0$ V				-0.5		0.5	μΑ	
t _{on}	Turnon time		$C_L = 100 \mu F$, $R_L = 20\Omega$			20			20		
t _{off}	Turnoff time		$C_L = 100 \ \mu F, \ R_L = 20 \Omega$			40			40	ms	

CURRENT LIMIT

PARAMETER	TEST CONDITIONS ⁽¹⁾	TP	S204x	A	TF	UNIT			
	PARAMETER	TEST CONDITIONS.	MIN	TYP	MAX	MIN	TYP	MAX	ONII
Ios	Short-circuit output current	V _{I(IN)} = 5 V, OUT connected to GND, Device enabled into short circuit	0.3	0.5	0.7	0.3	0.5	0.7	Α

⁽¹⁾ Pulse-testing techniques maintain junction temperature close to ambient temperature; thermal effects must be taken into account separately.



SUPPLY CURRENT (TPS2045A, TPS2055A)

DADAMETED		TEST COMP	ITIONS	TP	S2045A		Ti	PS2055	A	UNIT
PARAMETER		TEST CONDITIONS			TYP	MAX	MIN	TYP	MAX	UNII
		\/ \/	T _J = 25°C		0.025	1				
Supply current,	No Load	$V_{I(EN)} = V_{I(IN)}$	40°C ≤ T _J ≤ 125°C			10				^
low-level output	on OUT	.,	T _J = 25°C					0.025	1	μΑ
		$V_{I(EN)} = 0 V$	40°C ≤ T _J ≤ 125°C						10	
		.,	T _J = 25°C	·	85	110				
Supply current,	No Load	V _{I(€14)} = 0 V	40°C ≤ T _J ≤ 125°C	·	100					
high-level output	on OUT	V V	T _J = 25°C	·				85	110	μΑ
		$V_{I(EN)} = V_{I(IN)}$	40°C ≤ T _J ≤ 125°C	·				100		
	OUT	$V_{I(EN)} = V_{I(IN)}$	40°C ≤ T _J ≤ 125°C	·	100					
Leakage current	to ground	V _{I(EN)} = 0 V	40°C ≤ T _J ≤ 125°C	,				100		μΑ
Reverse leakage	IN = High	V _{I(EN)} = 0 V	T _ 25°C		0.3					^
current	impedance	V _{I(EN)} = V _{I(IN)}	$T_J = 25^{\circ}C$					0.3		μΑ

SUPPLY CURRENT (TPS2046A, TPS2056A)

DADAMETED		TEST CONDITIONS			PS2046	A	Т	UNIT			
PARAMETER					TYP	MAX	MIN	TYP	MAX	UNII	
		V V	$T_J = 25^{\circ}C$		0.025	1					
Supply current,	No Load	$V_{I(ENx)} = V_{I(IN)}$	40°C ≤ T _J ≤ 125°C			10				^	
low-level output	on OUT	V 0.V	T _J = 25°C					0.025	1	μΑ	
		$V_{I(ENx)} = 0 V$	40°C ≤ T _J ≤ 125°C						10		
		V 0.V	$T_J = 25^{\circ}C$		85	110					
Supply current,	No Load	$V_{I(ENx)} = 0 V$	40°C ≤ T _J ≤ 125°C		100					^	
high-level output	on OUT	., .,	T _J = 25°C					85	110	μΑ	
		$V_{I(ENx)} = V_{I(IN)}$	40°C ≤ T _J ≤ 125°C					100			
	OUT	$V_{I(ENx)} = V_{I(IN)}$	40°C ≤ T _J ≤ 125°C		100						
	connected to ground	V _{I(ENx)} = 0 V	40°C ≤ T _J ≤ 125°C					100		μΑ	
Reverse leakage	erse leakage $IN = high$ $V_{I(EN)} = 0 V$	V _{I(EIN)} = 0 V	T _{.1} = 25°C		0.3					^	
current	impedance	$V_{I(EN)} = V_{I(IN)}$	1] = 20 0					0.3		μΑ	



SUPPLY CURRENT (TPS2047A, TPS2057A)

DADAMETED		TEST CONDITI	IONS	Т	PS2047	Ά	Т	PS2057	Ά	UNIT
PARAMETER		TEST CONDITIONS					MIN	TYP	MAX	UNII
		V V	$T_J = 25^{\circ}C$		0.05	2				
Supply current,	No load on	$V_{I(ENx)} = V_{I(INx)}$	40°C ≤ T _J ≤ 125°C			20				^
low-level output	OUTx	.,	T _J = 25°C					0.05	2	μΑ
	Vı	$V_{I(ENx)} = 0 V$	40°C ≤ T _J ≤ 125°C						20	
		.,	$T_J = 25^{\circ}C$		160	200				
Supply current,	No load on	$A^{I(EIAX)} = 0$ A	40°C ≤ T _J ≤ 125°C		200					μΑ
high-level output	OUTx	V V	$T_J = 25^{\circ}C$					160	200	
		$V_{I(ENx)} = V_{I(INx)}$	40°C ≤ T _J ≤ 125°C					200		
	OUTx	$V_{I(ENx)} = V_{I(INx)}$	40°C ≤ T _J ≤ 125°C		200					
Leakage current	connected to ground	V _{I(ENx)} = 0 V	40°C ≤ T _J ≤ 125°C					200		μΑ
Reverse leakage	IN = high	V _{I(ENX)} = 0 V	T = 25°C		0.3					
current	impedance	$V_{I(ENx)} = V_{I(IN)}$	T _J = 25°C					0.3		μΑ

SUPPLY CURRENT (TPS2048A, TPS2058A)

PARAMETER		TEST CONDI	Т	PS2048	SA .	TF	UNIT			
TANAMETER		TEST CONDI	TIONS	MIN	TYP	MAX	MIN	TYP	MAX	UNII
		V V	T _J = 25°C		0.05	2				
Supply current,	No Load on	$V_{I(ENx)} = V_{I(INx)}$	40°C ≤ T _J ≤ 125°C			20				^
low-level output	OUTx	V _{I(ENx)} = 0 V	T _J = 25°C					0.05	2	μΑ
			40°C ≤ T _J ≤ 125°C						20	
			T _J = 25°C		170	220				
Supply current,	No Load on	$V_{I(ENx)} = 0 V$	40°C ≤ T _J ≤ 125°C		200					^
high-level output	OUTx	V V	T _J = 25°C					170	220	μΑ
		$V_{I(ENx)} = V_{I(INx)}$	40°C ≤ T _J ≤ 125°C					200		
	OUTx	$V_{I(ENx)} = V_{I(INx)}$	40°C ≤ T _J ≤ 125°C		200					
Leakage current	to ground	V _{I(ENx)} = 0 V	40°C ≤ T _J ≤ 125°C					200		μΑ
Reverse leakage	IN = high	V _{I(EN)} = 0 V	T = 25°C		0.3					^
current	impedance	$V_{I(EN)} = V_{I(IN)}$	T _J = 25°C					0.3		μΑ

UNDERVOLTAGE LOCKOUT

PARAMETER	TEST CONDITIONS	Т	PS204x	Α	TP	UNIT		
PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	MIN	TYP	MAX	UNIT
Low-level input voltage		2		2.5	2		2.5	V
Hysteresis	T _J = 25°C		100			100		mV

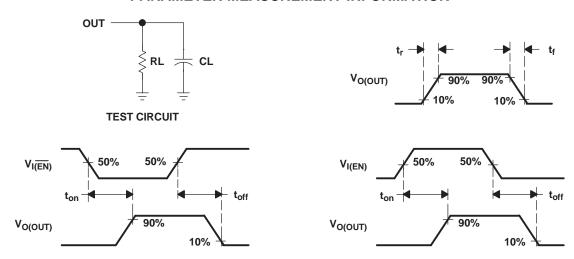
OVERCURRENT OC

PARAMETER	TEST CONDITIONS	Т	PS204x	κA	TP	UNIT		
	TEST CONDITIONS	MIN	TYP	MAX	MIN	TYP	MAX	UNII
Sink current ⁽¹⁾	V _O = 5 V			10			10	mA
Output low voltage	I _O = 5 V, V _{OL(OC)}			0.5			0.5	V
Off-state current ⁽¹⁾	V _O = 5 V, V _O = 3.3 V			1			1	μΑ

⁽¹⁾ Specified by design, not production tested.



PARAMETER MEASUREMENT INFORMATION



VOLTAGE WAVEFORMS

Figure 1. Test Circuit and Voltage Waveforms

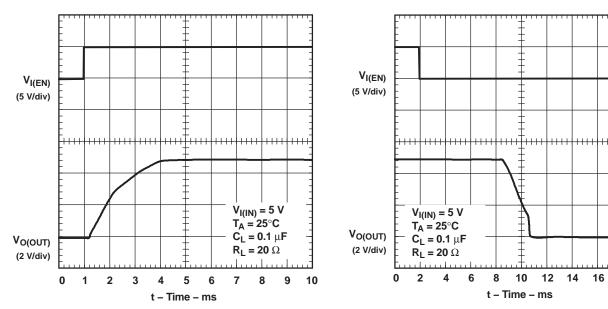


Figure 2. Turnon Delay and Rise Time With 0.1- μ F Load

Figure 3. Turnoff Delay and Rise Time With 0.1- μ F Load

18

20



PARAMETER MEASUREMENT INFORMATION (continued)

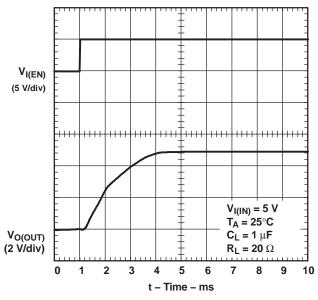


Figure 4. Turnon Delay and Rise Time With 1-μF Load

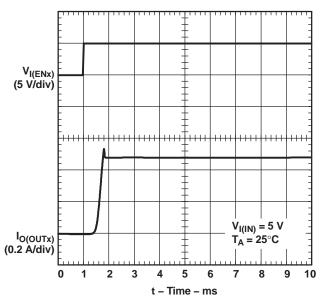


Figure 6. TPS2055A, Short-Circuit Current, Device Enabled Into Short

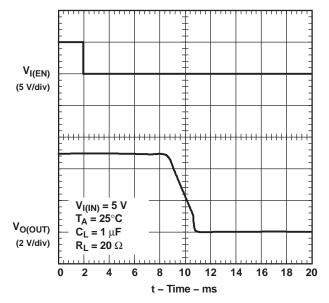


Figure 5. Turnoff Delay and Fall Time With 1-μF Load

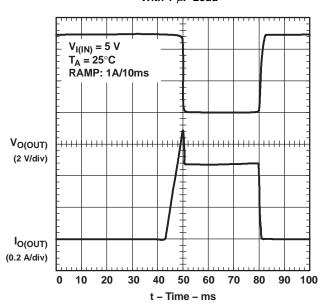


Figure 7. TPS2055A, Threshold Trip Current With Ramped Load on Enabled Device



PARAMETER MEASUREMENT INFORMATION (continued)

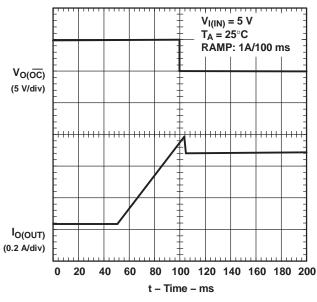


Figure 8. OC Response With Ramped Load on Enabled Device

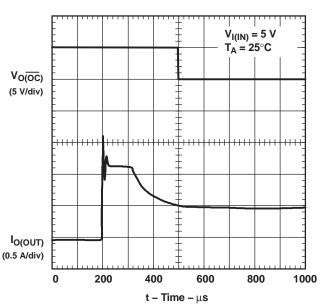


Figure 10. 4-Ω Load Connected to Enabled Device

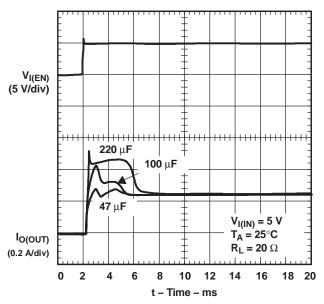


Figure 9. Inrush Current With 47-μF, 100-μF and 220-μF Load Capacitance

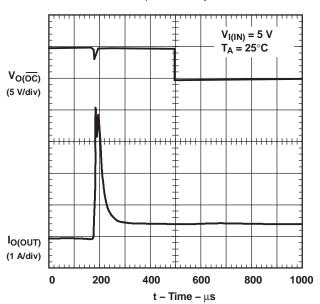
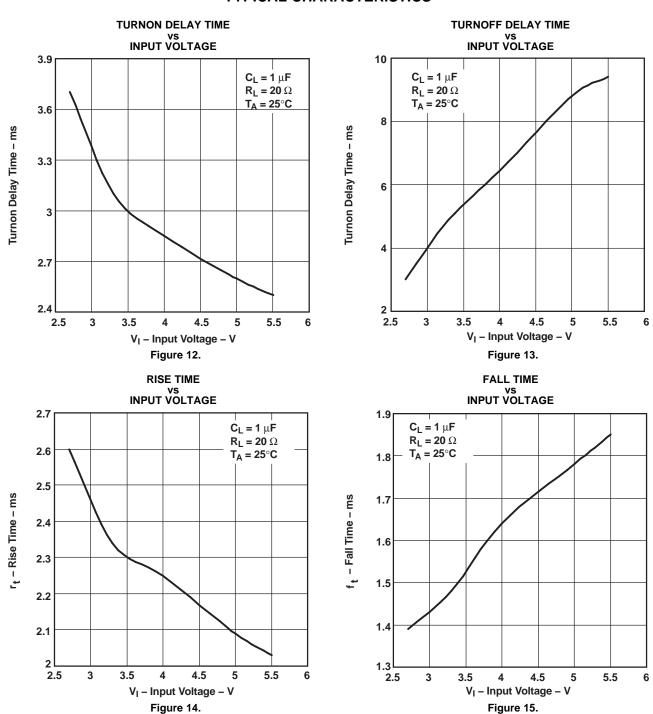


Figure 11. 1-Ω Load Connected to Enabled Device

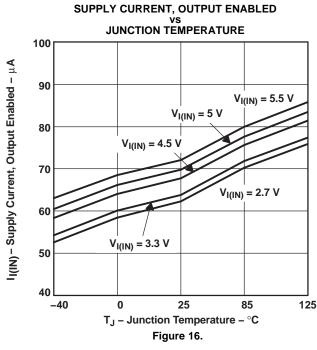


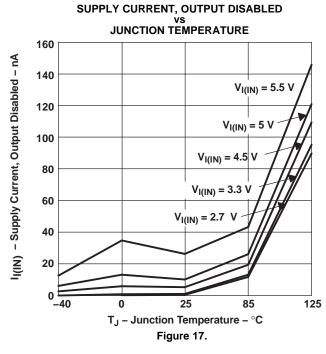
TYPICAL CHARACTERISTICS

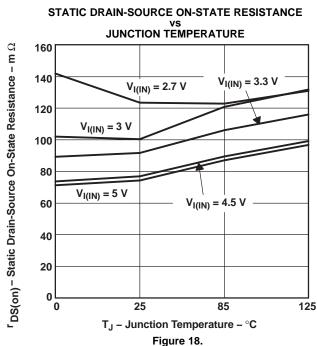


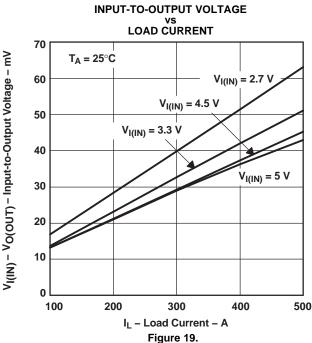


TYPICAL CHARACTERISTICS (continued)



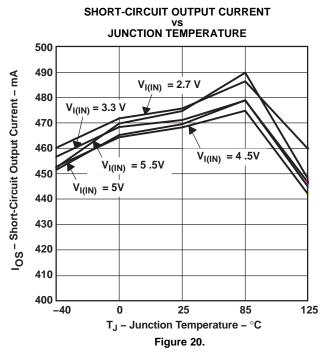


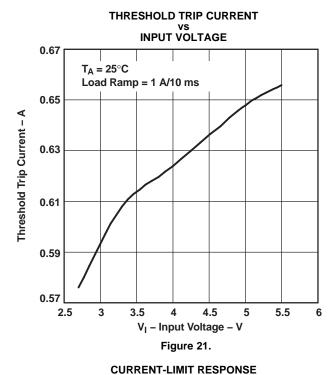


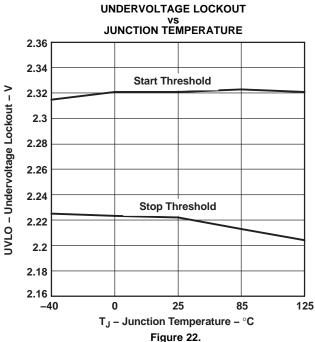


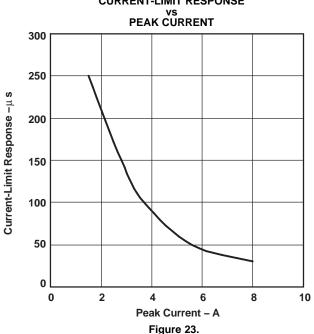


TYPICAL CHARACTERISTICS (continued)











APPLICATION INFORMATION

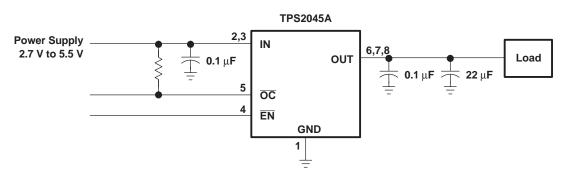


Figure 24. Typical Application (Example, TPS2045A)

POWER-SUPPLY CONSIDERATIONS

A 0.01- μF to 0.1- μF ceramic bypass capacitor between INx and GND, close to the device, is recommended. Placing a high-value electrolytic capacitor on the output pin(s) is recommended when the output load is heavy. This precaution reduces power-supply transients that may cause ringing on the input. Additionally, bypassing the output with a 0.01- μF to 0.1- μF ceramic capacitor improves the immunity of the device to short-circuit transients.

OVERCURRENT

A sense FET is employed to check for overcurrent conditions. Unlike current-sense resistors, sense FETs do not increase the series resistance of the current path. When an overcurrent condition is detected, the device maintains a constant output current and reduces the output voltage accordingly. Complete shutdown occurs only if the fault is present long enough to activate thermal limiting.

Three possible overload conditions can occur. In the first condition, the output has been shorted before the device is enabled or before $V_{I(IN)}$ has been applied (see Figure 6). The TPS204xA and TPS205xA sense the short and immediately switch into a constant-current output.

In the second condition, a short or an overload occurs while the device is enabled. At the instant the overload occurs, very high currents may flow for a short time before the current-limit circuit can react. After the current-limit circuit has tripped (reached the overcurrent trip threshold) the device switches into constant-current mode.

In the third condition, the load has been gradually increased beyond the recommended operating current. The current is permitted to rise until the current-limit threshold is reached or until the thermal limit of the device is exceeded (see Figure 7). The TPS204xA and TPS205xA are capable of delivering current up to the current-limit threshold without damaging the device. Once the threshold has been reached, the device switches into its constant-current mode.

OC RESPONSE

The $\overline{\text{OC}}$ open-drain output is asserted (active low) when an overcurrent or over temperature condition is encountered. The output will remain asserted until the overcurrent or over temperature condition is removed. Connecting a heavy capacitive load to an enabled device can cause momentary false overcurrent reporting from the inrush current flowing through the device, charging the downstream capacitor. The TPS204xA and TPS205xA family of devices are designed to reduce false overcurrent reporting. An internal overcurrent transient filter eliminates the need for external components to remove unwanted pulses. Using low-ESR electrolytic capacitors on the output lowers the inrush current flow through the device during hot-plug events by providing a low-impedance energy source, also reducing erroneous overcurrent reporting.



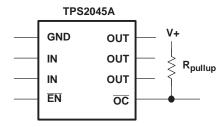


Figure 25. Typical Circuit for OC Pin (Example, TPS2045A)

POWER DISSIPATION AND JUNCTION TEMPERATURE

The low on-resistance on the n-channel MOSFET allows small surface-mount packages, such as SOIC, to pass large currents. The thermal resistance of these packages is high compared to those of power packages; it is good design practice to check power dissipation and junction temperature. Begin by determining the $r_{DS(on)}$ of the N-channel MOSFET relative to the input voltage and operating temperature. As an initial estimate, use the highest operating ambient temperature of interest and read $r_{DS(on)}$ from Figure 18. Using this value, the power dissipation per switch can be calculated by:

$$\mathsf{P}_\mathsf{D} = \mathsf{r}_\mathsf{DS(on)} \times \mathsf{I}^2$$

Depending on which device is being used, multiply this number by the number of switches being used. This step will render the total power dissipation from the N-channel MOSFETs.

Finally, calculate the junction temperature:

$$T_J = P_D \times R_{\theta,JA} + T_A$$

Where: T_A = Ambient temperature °C $R_{\Theta JA}$ = Thermal resistance SOIC = 172°C/W (for 8 pin), 111°C/W (for 16 pin) P_D = Total power dissipation based on number of switches being used.

Compare the calculated junction temperature with the initial estimate. If they do not agree within a few degrees, repeat the calculation, using the calculated value as the new estimate. Two or three iterations are generally sufficient to get a reasonable answer.

THERMAL PROTECTION

Thermal protection prevents damage to the IC when heavy-overload or short-circuit faults are present for extended periods of time. The faults force the TPS204xA and TPS205xA into constant-current mode, which causes the voltage across the high-side switch to increase; under short-circuit conditions, the voltage across the switch is equal to the input voltage. The increased dissipation causes the junction temperature to rise to high levels. The protection circuit senses the junction temperature of the switch and shuts it off. Hysteresis is built into the thermal sense circuit, and after the device has cooled approximately 20 degrees, the switch turns back on. The switch continues to cycle in this manner until the load fault or input power is removed.

The TPS204xA and TPS205xA implement a dual thermal trip to allow fully independent operation of the power distribution switches. In an overcurrent or short-circuit condition the junction temperature will rise. Once the die temperature rises to approximately 140°C, the internal thermal sense circuitry checks which power switch is in an overcurrent condition and turns that power switch off, thus isolating the fault without interrupting operation of the adjacent power switch. Should the die temperature exceed the first thermal trip point of 140°C and reach 160°C, both switches turn off. The \overline{OC} open-drain output is asserted (active low) when overtemperature or overcurrent occurs.

UNDERVOLTAGE LOCKOUT (UVLO)

An undervoltage lockout ensures that the power switch is in the off state at power up. Whenever the input voltage falls below approximately 2 V, the power switch will be quickly turned off. This facilitates the design of hot-insertion systems where it is not possible to turn off the power switch before input power is removed. The UVLO will also keep the switch from being turned on until the power supply has reached at least 2 V, even if the switch is enabled. Upon reinsertion, the power switch will be turned on, with a controlled rise time to reduce EMI and voltage overshoots.



UNIVERSAL SERIAL BUS (USB) APPLICATIONS

The universal serial bus (USB) interface is a 12-Mb/s, or 1.5-Mb/s, multiplexed serial bus designed for low-to-medium bandwidth PC peripherals (e.g., keyboards, printers, scanners, and mice). The four-wire USB interface is conceived for dynamic attach-detach (hot plug-unplug) of peripherals. Two lines are provided for differential data, and two lines are provided for 5-V power distribution.

USB data is a 3.3-V level signal, but power is distributed at 5 V to allow for voltage drops in cases where power is distributed through more than one hub across long cables. Each function must provide its own regulated 3.3 V from the 5-V input or its own internal power supply.

The USB specification defines the following five classes of devices, each differentiated by power-consumption requirements:

- Hosts/self-powered hubs (SPH)
- Bus-powered hubs (BPH)
- · Low-power, bus-powered functions
- High-power, bus-powered functions
- Self-powered functions

Self-powered and bus-powered hubs distribute data and power to downstream functions. The TPS204xA and TPS205xA can provide power-distribution solutions for many of these classes of devices.

HOST/SELF-POWERED AND BUS-POWERED HUBS

Hosts and self-powered hubs have a local power supply that powers the embedded functions and the downstream ports. This power supply must provide from 5.25 V to 4.75 V to the board side of the downstream connection under full-load and no-load conditions. Hosts and SPHs are required to have current-limit protection and must report overcurrent conditions to the USB controller. Typical SPHs are desktop PCs, monitors, printers, and stand-alone hubs.

Bus-powered hubs obtain all power from upstream ports and often contain an embedded function. The hubs are required to power up with less than one unit load. The BPH usually has one embedded function, and power is always available to the controller of the hub. If the embedded function and hub require more than 100 mA on power up, the power to the embedded function may need to be kept off until enumeration is completed. This can be accomplished by removing power or by shutting off the clock to the embedded function. Power switching the embedded function is not necessary if the aggregate power draw for the function and controller is less than one unit load. The total current drawn by the bus-powered device is the sum of the current to the controller, the embedded function, and the downstream ports, and it is limited to 500 mA from an upstream port.

LOW-POWER BUS-POWERED FUNCTIONS AND HIGH-POWER BUS-POWERED FUNCTIONS

Both low-power and high-power bus-powered functions obtain all power from upstream ports; low-power functions always draw less than 100 mA (see Figure 26); high-power functions must draw less than 100 mA at power up and can draw up to 500 mA after enumeration. If the load of the function is more than the parallel combination of 44 Ω and 10 μ F at power up, the device must implement inrush current limiting.

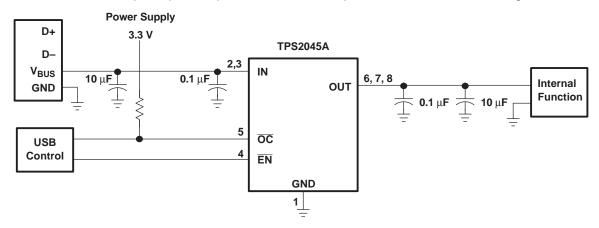


Figure 26. Low-Power Bus-Powered Function (Example, TPS2045A)

SLVS251C-SEPTEMBER 2000-REVISED JANUARY 2008



USB POWER-DISTRIBUTION REQUIREMENTS

USB can be implemented in several ways, and, regardless of the type of USB device being developed, several power-distribution features must be implemented.

- Hosts/self-powered hubs must:
 - Current-limit downstream ports
 - Report overcurrent conditions on USB V_{BUS}
 - Enable/disable power to downstream ports
 - Power up at <100 mA
 - Limit inrush current ($<44 \Omega$ and 10 μ F)
 - Limit inrush currents
 - Power up at <100 mA
- Bus-powered hubs must:
 - Enable/disable power to downstream ports
 - Power up at <100 mA
 - Limit inrush current ($<44 \Omega$ and 10 μ F)
 - Limit inrush currents
 - Power up at <100 mA
- Functions must:
 - Limit inrush currents
 - Power up at <100 mA

The feature set of the TPS204xA and TPS205xA allows them to meet each of these requirements. The integrated current-limiting and overcurrent reporting is required by hosts and self-powered hubs. The logic-level enable and controlled rise times meet the need of both input and output ports on bus-power hubs, as well as the input ports for bus-power functions.



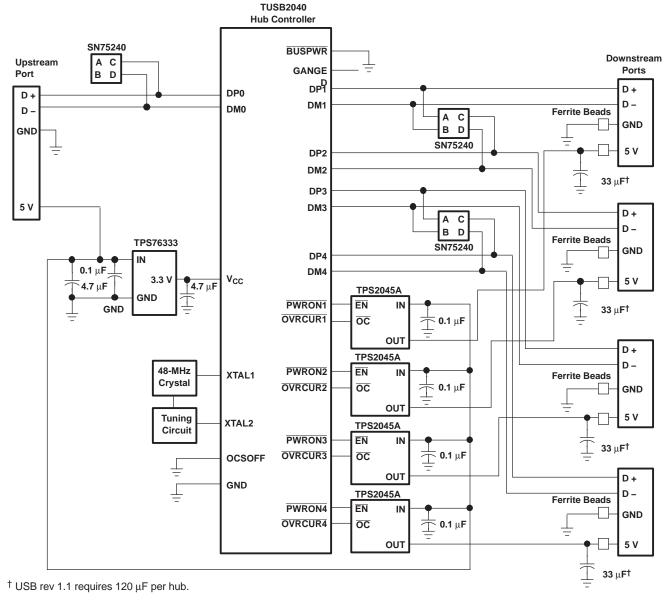


Figure 27. Bus-Powered Hub Implementation, TPS2045A



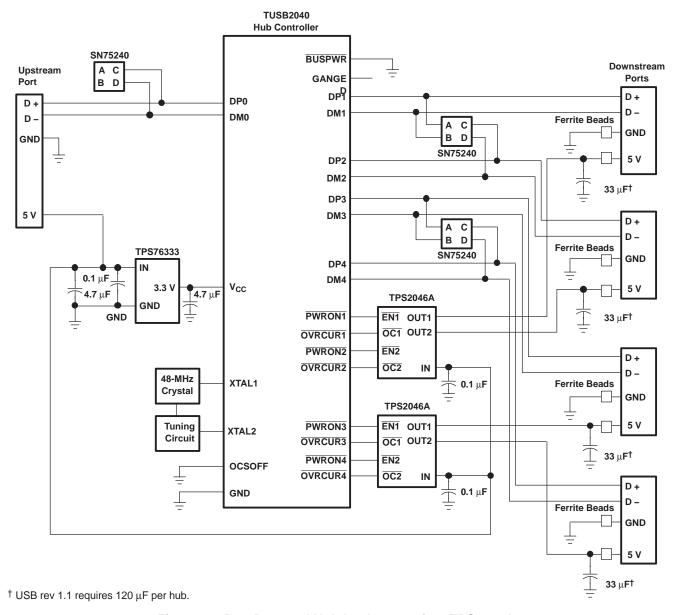
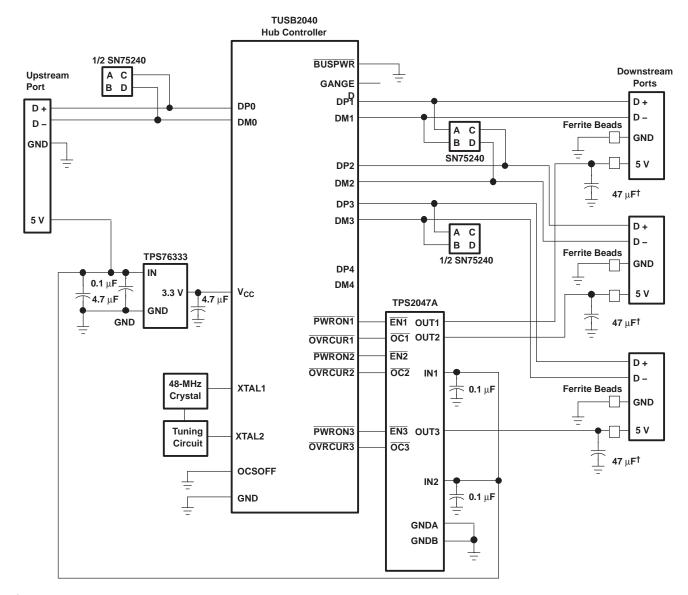


Figure 28. Bus-Powered Hub Implementation, TPS2046A





 $^{^\}dagger$ USB rev 1.1 requires 120 μF per hub.

Figure 29. Bus-Powered Hub Implementation, TPS2047A



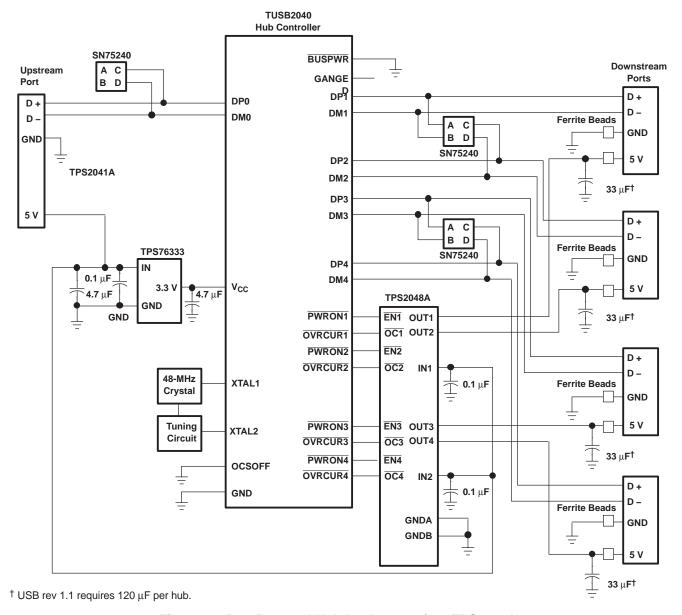


Figure 30. Bus-Powered Hub Implementation, TPS2048A



GENERIC HOT-PLUG APPLICATIONS (see Figure 31)

In many applications it may be necessary to remove modules or pc boards while the main unit is still operating. These are considered hot-plug applications. Such implementations require the control of current surges seen by the main power supply and the card being inserted. The most effective way to control these surges is to limit and slowly ramp the current and voltage being applied to the card, similar to the way in which a power supply normally turns on. Due to the controlled rise times and fall times of the TPS204xA and TPS205xA, these devices can be used to provide a softer start-up to devices being hot-plugged into a powered system. The UVLO feature of the TPS204xA and TPS205xA also ensures the switch will be off after the card has been removed, and the switch will be off during the next insertion. The UVLO feature insures a soft start with a controlled rise time for every insertion of the card or module.

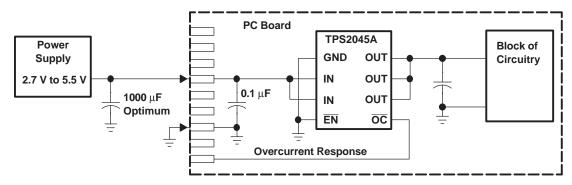


Figure 31. Typical Hot-Plug Implementation (Example, TPS2045A)

By placing the TPS204xA and TPS205xA between the V_{CC} input and the rest of the circuitry, the input power will reach these devices first after insertion. The typical rise time of the switch is approximately 2.5 ms, providing a slow voltage ramp at the output of the device. This implementation controls system surge currents and provides a hot-plugging mechanism for any device.





24-Aug-2014

PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead/Ball Finish (6)	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Sample
TPS2045AD	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 85	2045A	Sample
TPS2045ADG4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 85	2045A	Sample
TPS2045ADR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 85	2045A	Sampl
TPS2045ADRG4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 85	2045A	Sampl
TPS2046AD	NRND	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 85	2046A	
TPS2047ADR	NRND	SOIC	D	16	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 85	2047A	
TPS2047ADRG4	NRND	SOIC	D	16	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 85	2047A	
TPS2048AD	ACTIVE	SOIC	D	16	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 85	2048A	Samp
TPS2048ADR	ACTIVE	SOIC	D	16	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 85	2048A	Samp
TPS2048ADRG4	ACTIVE	SOIC	D	16	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 85	2048A	Samp
TPS2055AD	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 85	2055A	Samp
TPS2055ADG4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 85	2055A	Samp
TPS2055ADR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 85	2055A	Samp
TPS2055ADRG4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 85	2055A	Samp
TPS2056AD	NRND	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 85	2056A	
TPS2056ADG4	NRND	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 85	2056A	
TPS2056ADR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 85	2056A	Samp



PACKAGE OPTION ADDENDUM

24-Aug-2014

Orderable Device	Status	Package Type	_	Pins	Package	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
	(1)		Drawing		Qty	(2)	(6)	(3)		(4/5)	
TPS2056ADRG4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 85	2056A	Samples
TPS2057AD	ACTIVE	SOIC	D	16	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 85	2057A	Samples
TPS2057ADG4	ACTIVE	SOIC	D	16	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 85	2057A	Samples
TPS2057ADR	ACTIVE	SOIC	D	16	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 85	2057A	Samples
TPS2058AD	ACTIVE	SOIC	D	16	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 85	2058A	Samples
TPS2058ADG4	ACTIVE	SOIC	D	16	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 85	2058A	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes. **Pb-Free** (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.



PACKAGE OPTION ADDENDUM

24-Aug-2014

(6) Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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PACKAGE MATERIALS INFORMATION

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TAPE AND REEL INFORMATION





	Dimension designed to accommodate the component width
	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

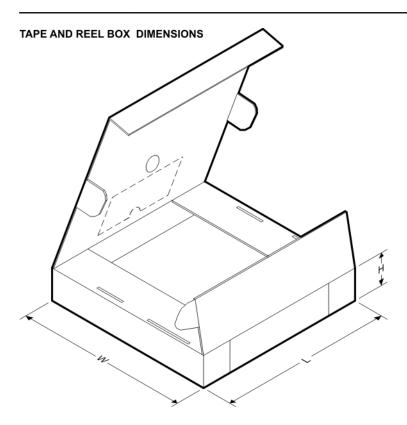
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TPS2045ADR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
TPS2047ADR	SOIC	D	16	2500	330.0	16.4	6.5	10.3	2.1	8.0	16.0	Q1
TPS2048ADR	SOIC	D	16	2500	330.0	16.4	6.5	10.3	2.1	8.0	16.0	Q1
TPS2055ADR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
TPS2056ADR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
TPS2056ADR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
TPS2057ADR	SOIC	D	16	2500	330.0	16.4	6.5	10.3	2.1	8.0	16.0	Q1

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*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TPS2045ADR	SOIC	D	8	2500	340.5	338.1	20.6
TPS2047ADR	SOIC	D	16	2500	333.2	345.9	28.6
TPS2048ADR	SOIC	D	16	2500	333.2	345.9	28.6
TPS2055ADR	SOIC	D	8	2500	340.5	338.1	20.6
TPS2056ADR	SOIC	D	8	2500	340.5	338.1	20.6
TPS2056ADR	SOIC	D	8	2500	367.0	367.0	35.0
TPS2057ADR	SOIC	D	16	2500	333.2	345.9	28.6

D (R-PDS0-G16)

PLASTIC SMALL OUTLINE



- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
- E. Reference JEDEC MS-012 variation AC.



D (R-PDSO-G16)

PLASTIC SMALL OUTLINE



- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



D (R-PDSO-G8)

PLASTIC SMALL OUTLINE



- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
- E. Reference JEDEC MS-012 variation AA.



D (R-PDSO-G8)

PLASTIC SMALL OUTLINE



- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



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Welcome to visit www.ameya360.com

Contact Us:

> Address:

401 Building No.5, JiuGe Business Center, Lane 2301, Yishan Rd Minhang District, Shanghai , China

> Sales:

Direct +86 (21) 6401-6692

Email amall@ameya360.com

QQ 800077892

Skype ameyasales1 ameyasales2

Customer Service :

Email service@ameya360.com

Partnership :

Tel +86 (21) 64016692-8333

Email mkt@ameya360.com